



The Search for True Chemicurrent from Catalytic Nanodiodes

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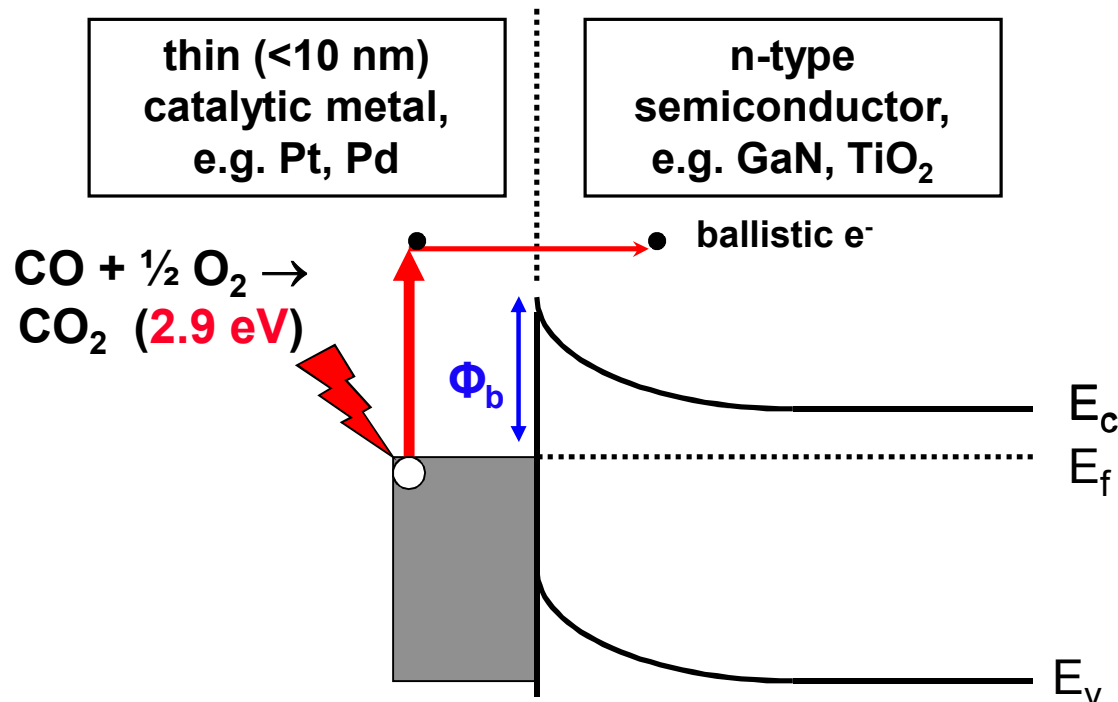
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GaN deposition – Dan Koleske

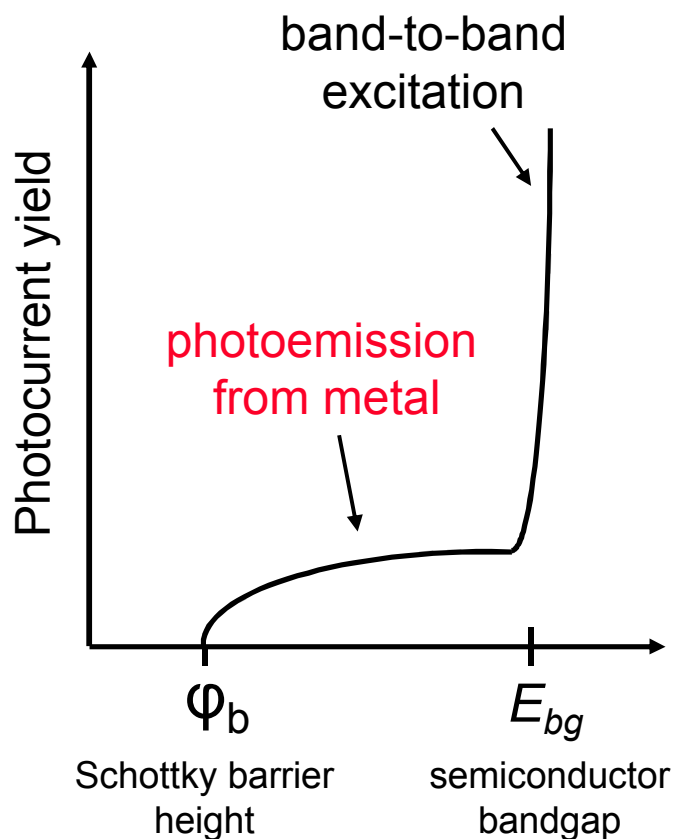
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What is a “Catalytic Nanodiode”?

- The catalytic nanodiode is a simple Schottky diode that converts chemical energy directly into electrical energy, via electronic excitation, **i.e. hot electrons**
- Somorjai et al. reported (2005) a reaction quantum yield (electrons/ CO_2) up to ~75% for the CO oxidation reaction on Pt/ TiO_2 , coined the term “catalytic nanodiode”

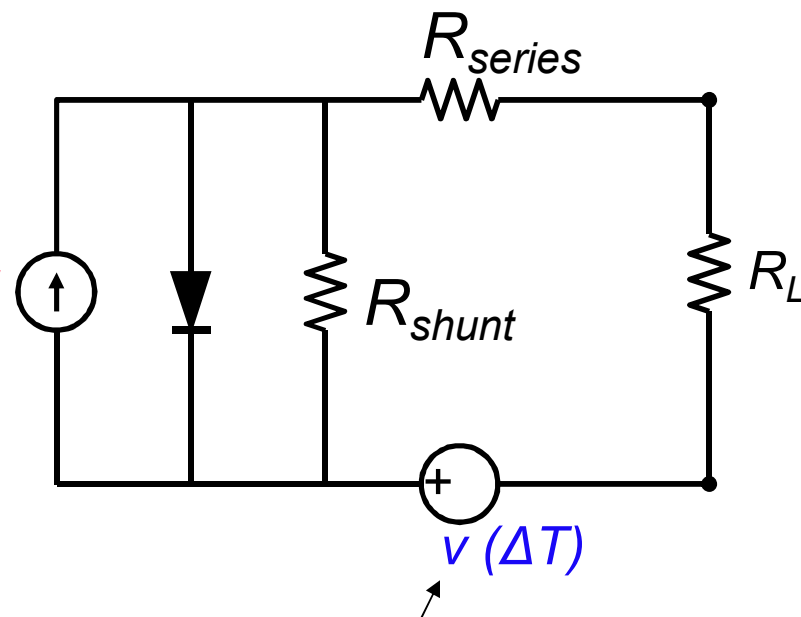


Best analogy to catalytic nanodiode is a **Schottky diode solar cell or photodiode** with sub-bandgap illumination



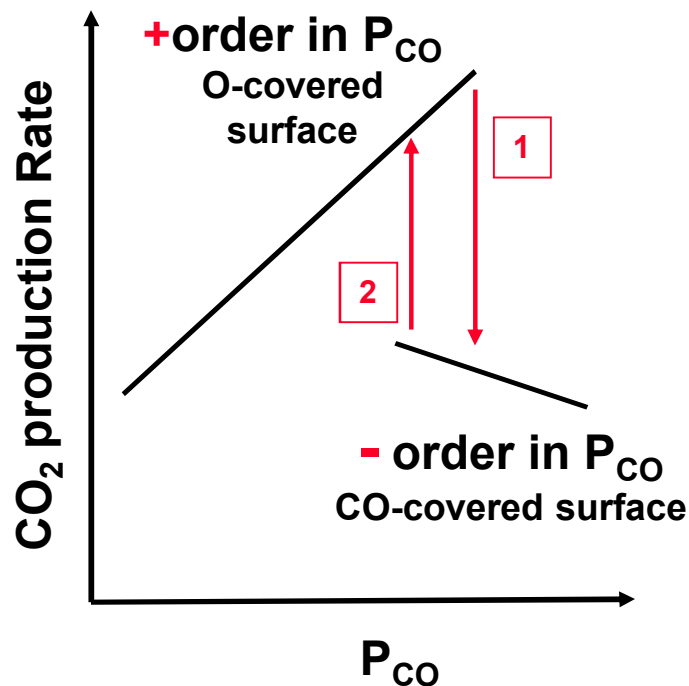
replace
photocurrent
with *i*
chemicurrent

equivalent circuit



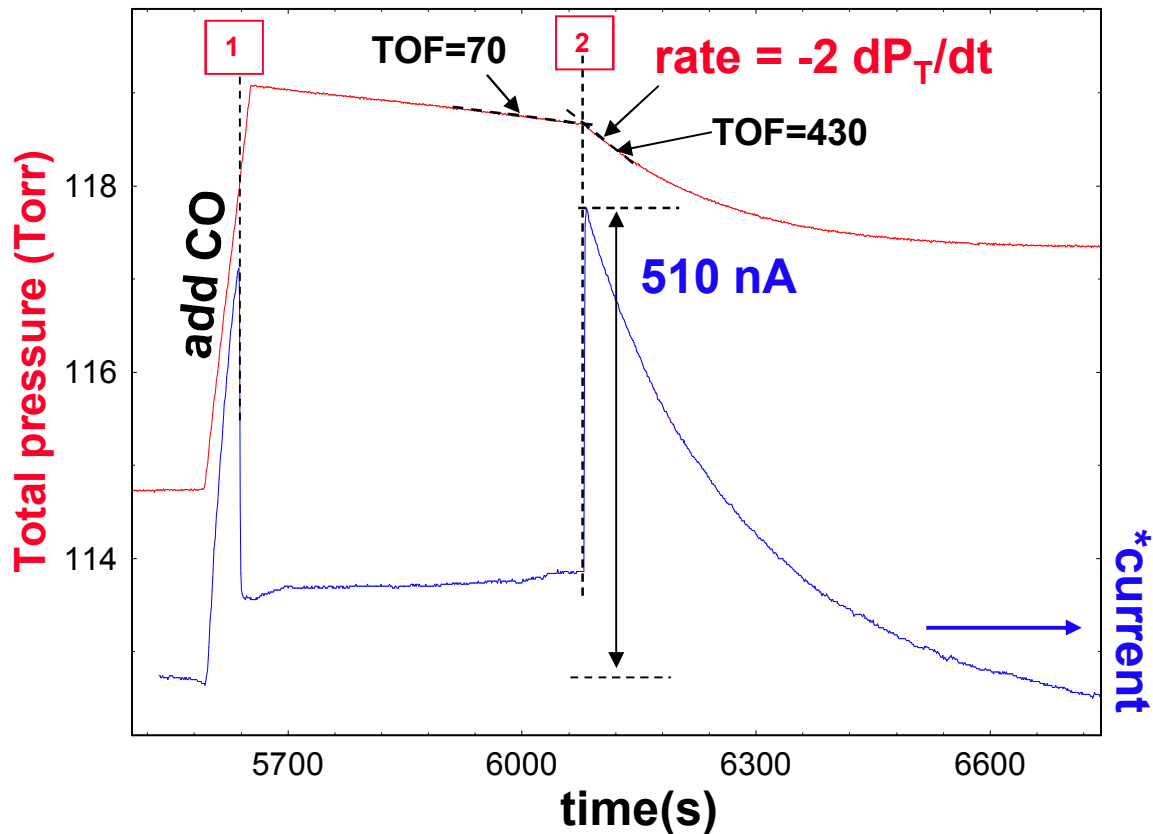
thermoelectric voltage,
typically 0.3-1.0 mV
before reaction conditions

Kinetic phase transition during CO oxidation on Pt is observable using the nanodiode current



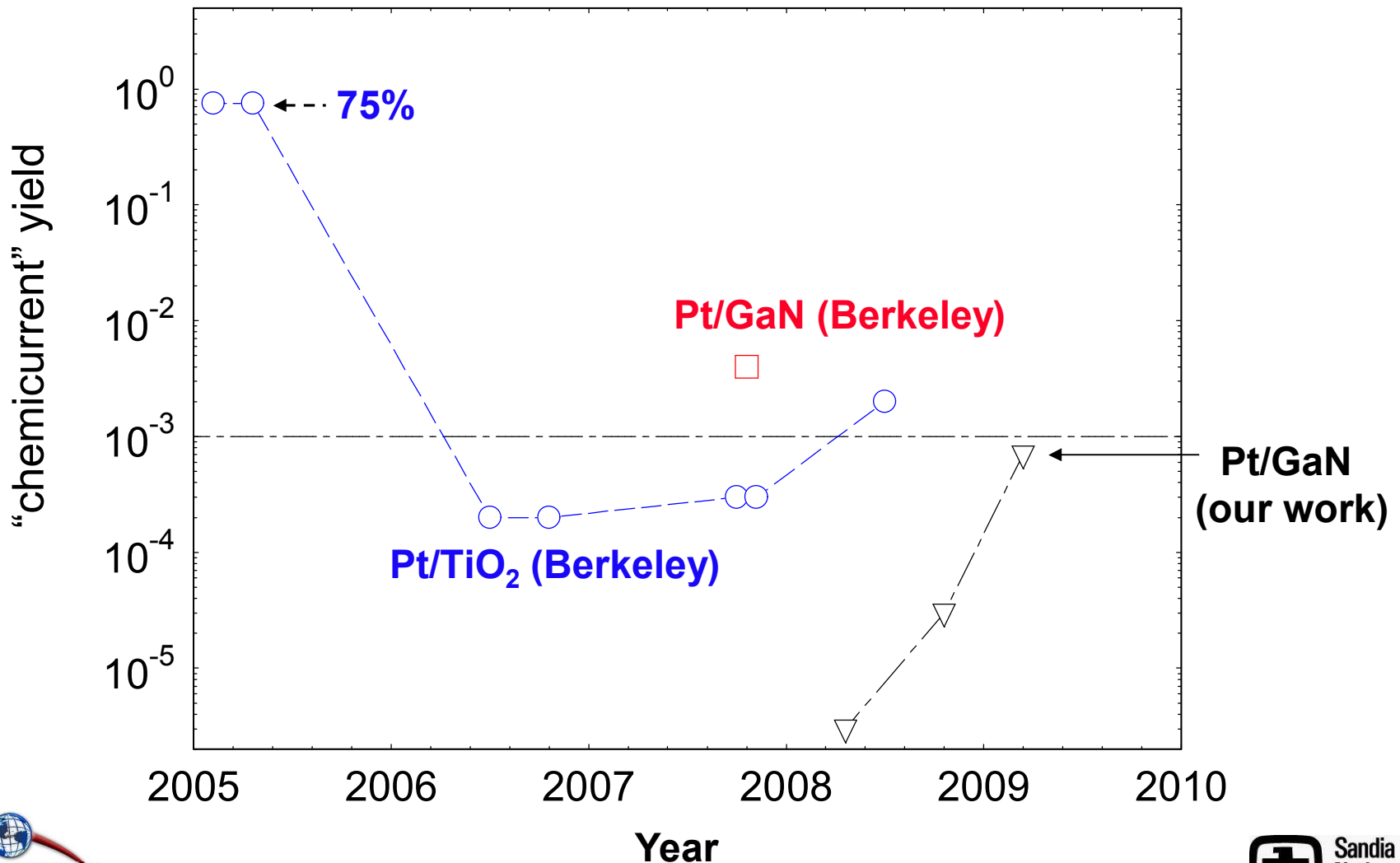
ref: e.g. Creighton JPC 1981

5 nm Pt/GaN nanodiode, 270°C

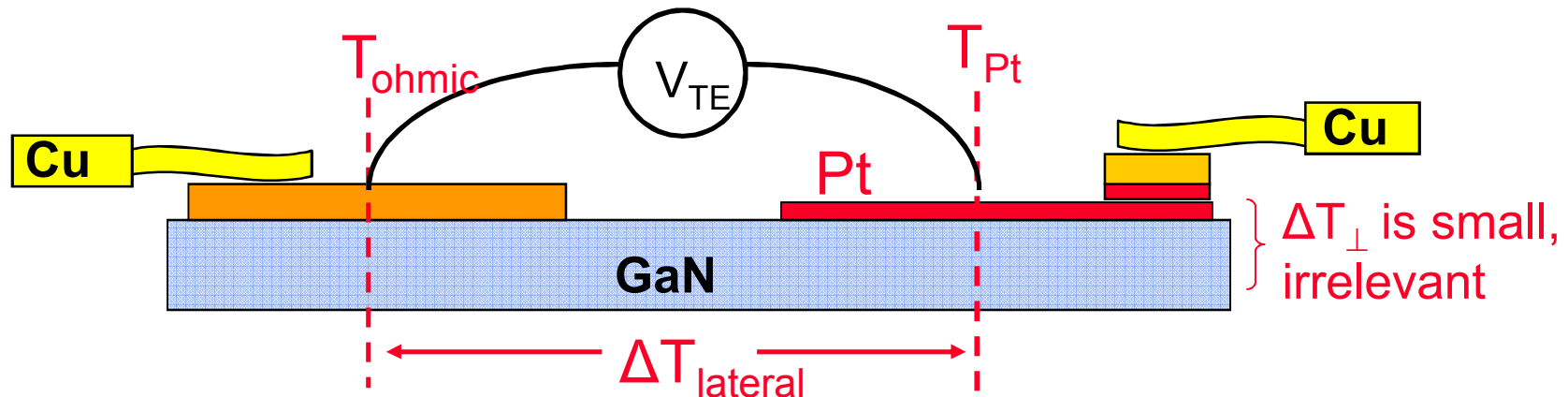


we use this lineshape as a fingerprint

Our yield measurements are in reasonable agreement with more recent Somorjai results (post 2005)



Is the electronic signal due to “chemicurrent”
or is it derived from a voltage source?



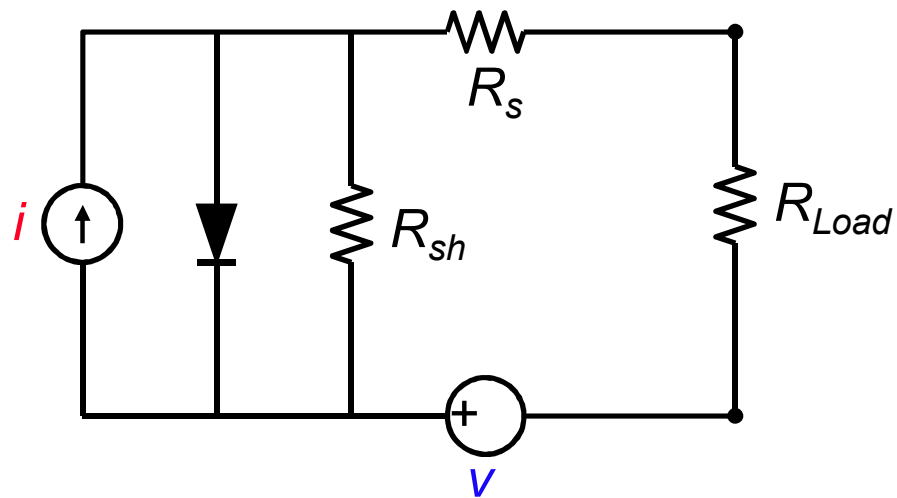
$$V_{TE} \sim (S_{GaN} - S_{Cu})\Delta T_{lat} + \text{much smaller terms}$$

V_{TE} is mostly determined by:

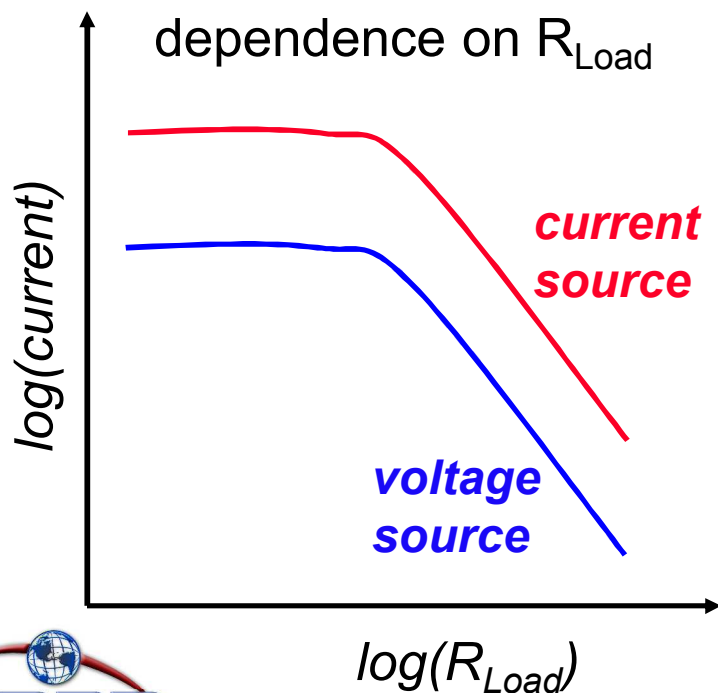
- 1) GaN Seebeck coefficient; S_{GaN} [typically $\sim -400 \mu V/deg$]
- 2) the lateral temperature difference, ΔT_{lat}

only need $\Delta T_{lat} \sim 1^{\circ}C$

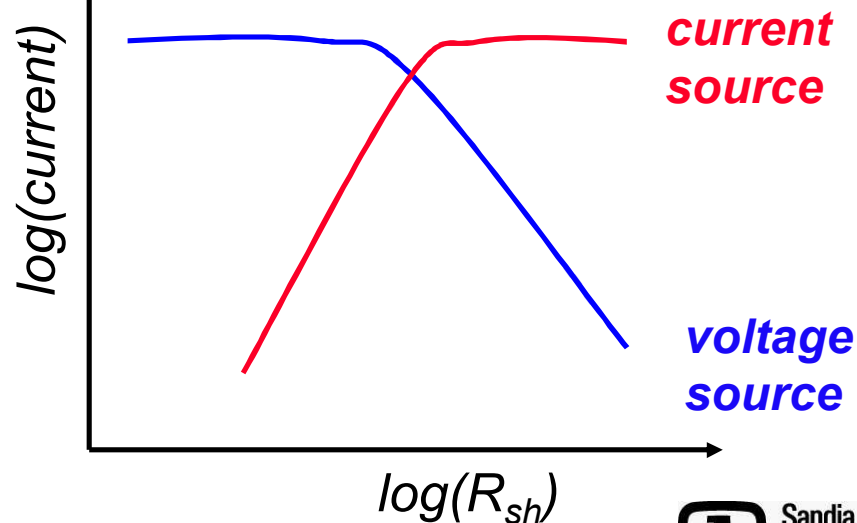
How can you differentiate a current source from a voltage source when shunt (R_{sh}) and series (R_s) resistance are present?



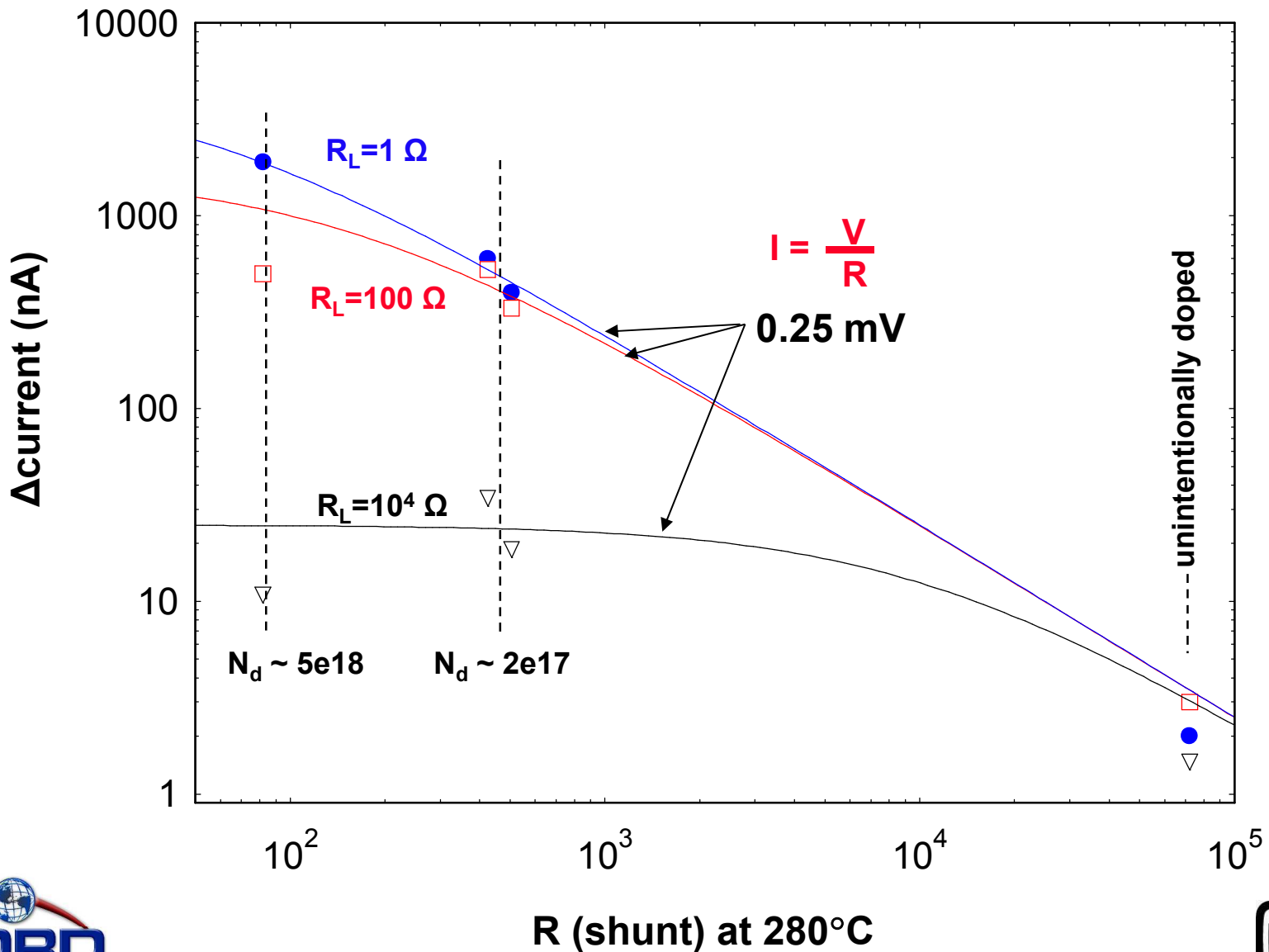
Both show same dependence on R_{Load}



But different dependence on R_{sh} (not simple to vary)



Vary R_{shunt} by varying GaN doping level,
behavior is indicative of a voltage source





The 2 Burning Questions

What is the magnitude of the Pt temperature rise,
 ΔT_{Pt} , during reaction?

How much is the lateral temperature gradient,
 ΔT_{lat} , affected by the reaction?

Reaction is exothermic; 68 kcal/mole, $\sim 2.9\text{eV}/\text{CO}_2$

For reaction TOF = 400, power density is $300\text{ mW}/\text{cm}^2$

For reference: heater is dissipating $700\text{ mW}/\text{cm}^2$ at 270°C

The heat liberated only needs to increase ΔT_{lat} by $\sim 1^\circ\text{C}$ in order to generate the measured signals



We use both theoretical and experimental methods to address these 2 questions

Theoretical:

“Simple” 1D and quasi-2D calculations

Full 3D simulations of entire reactor

Experimental:

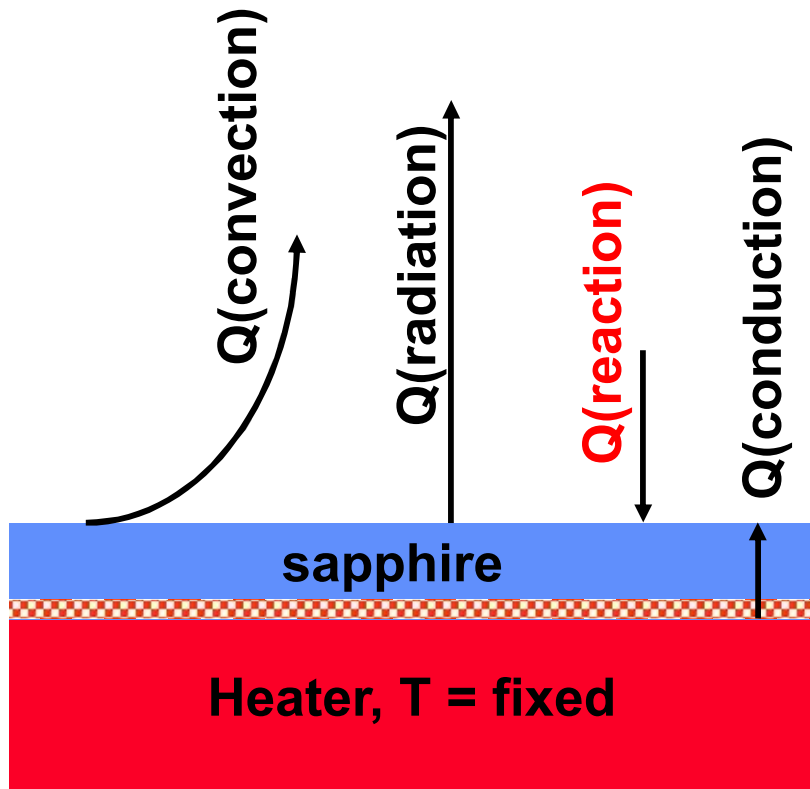
mid-IR optical pyrometry of Pt surface: ΔT_{Pt}

Thermocouple measurements of electrical contacts: ΔT_{lat}

1D calculation with isothermal heater

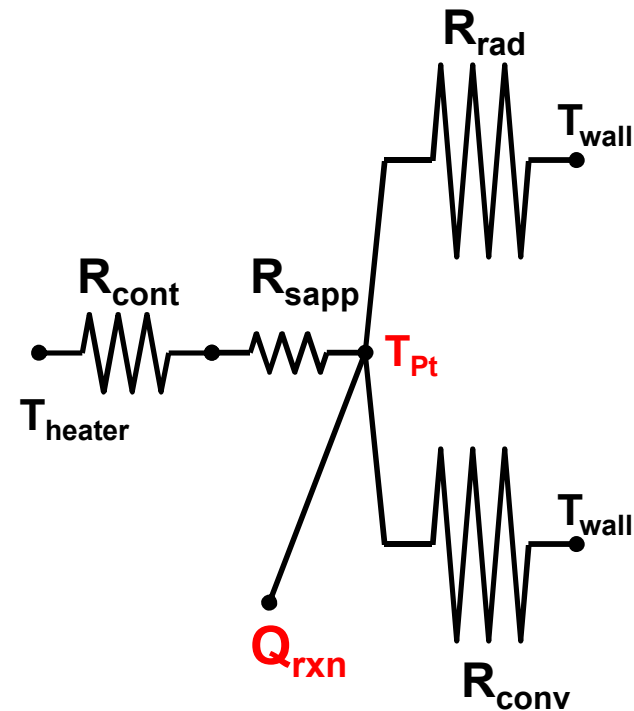
Physical model

chamber wall, $T = \text{fixed}$

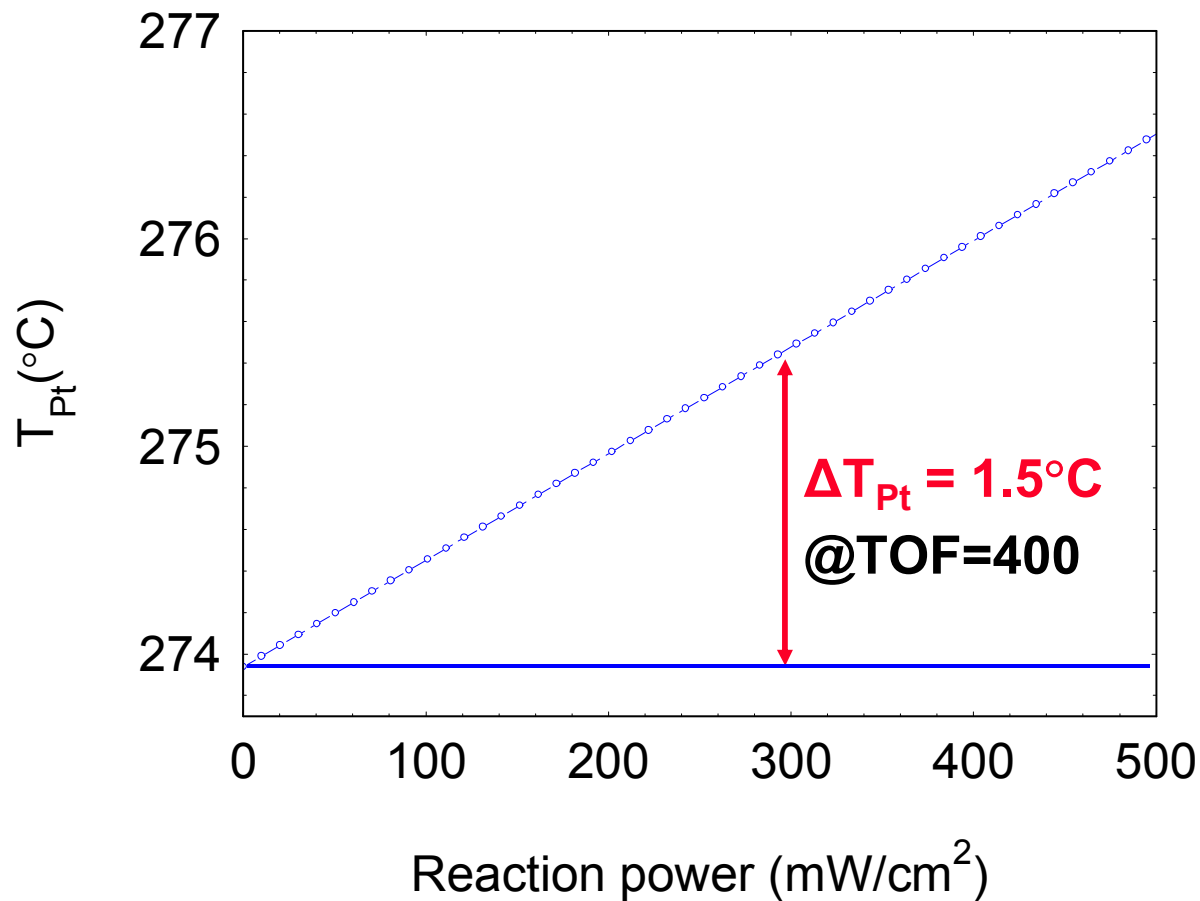


Equivalent thermal circuit

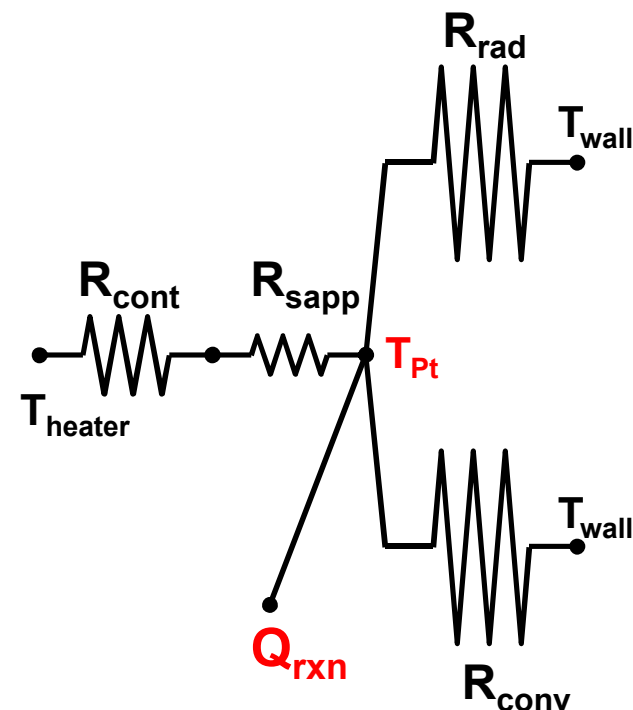
$$\Delta T = Q \cdot R_{\text{thermal}}$$



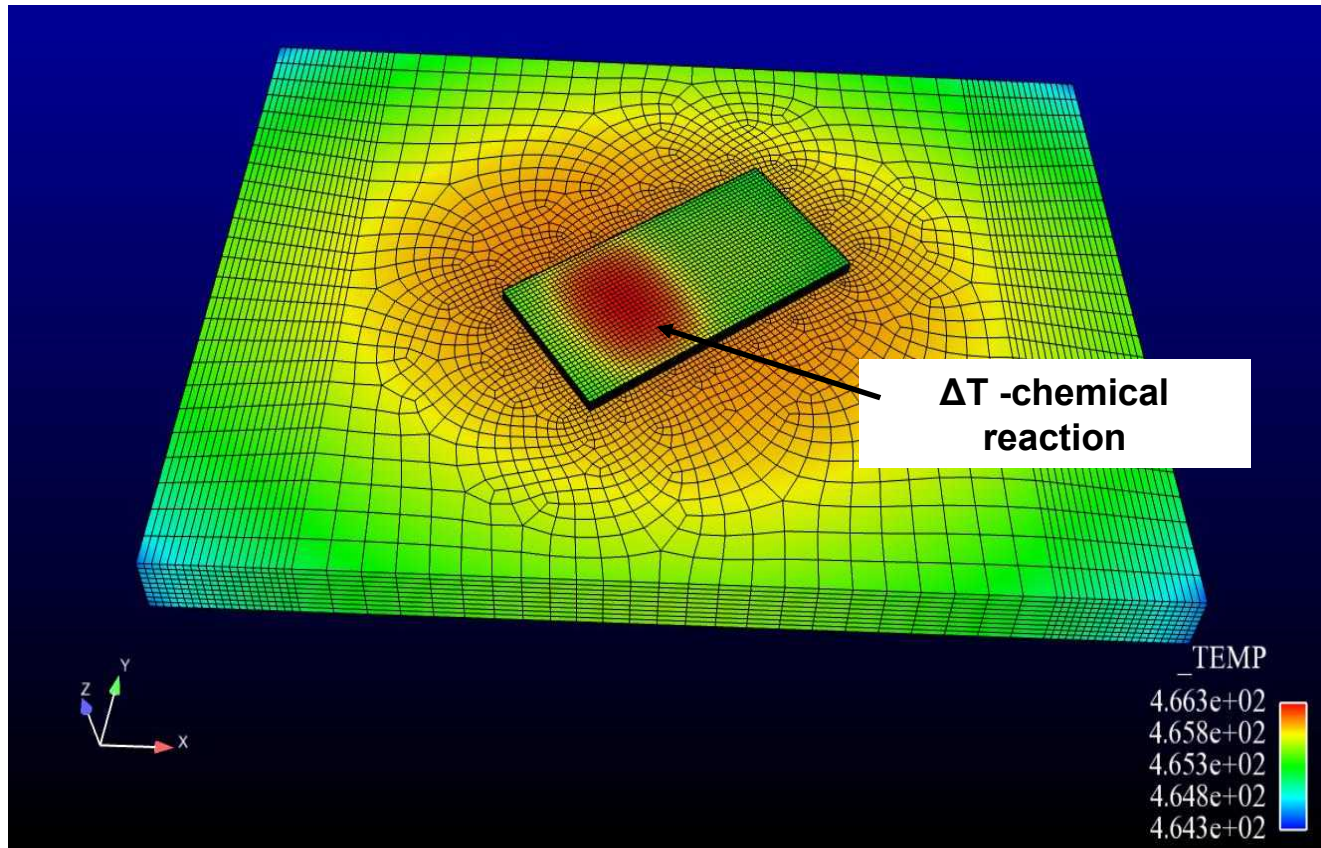
1D calculation with isothermal heater



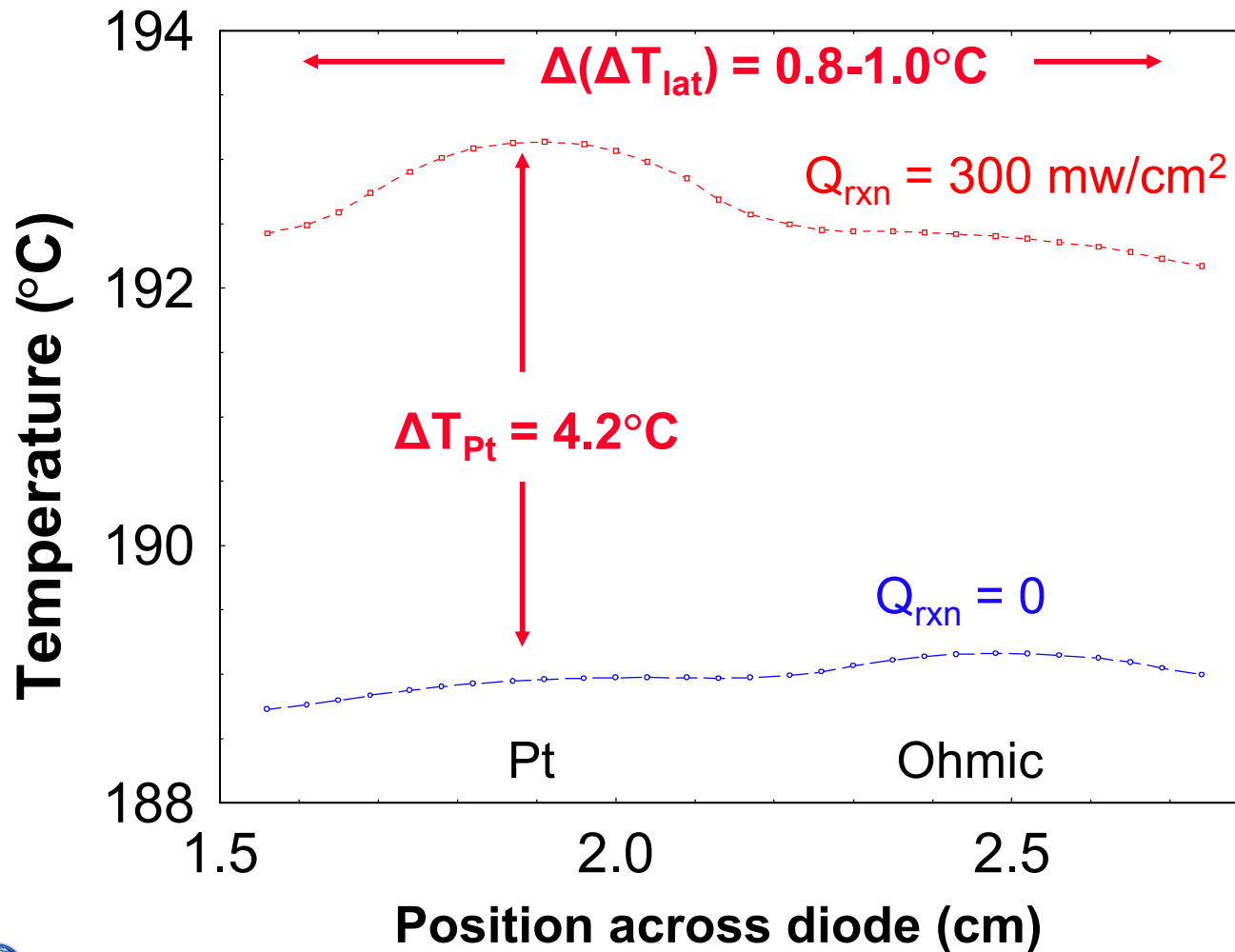
Equivalent thermal circuit



Full 3D simulation



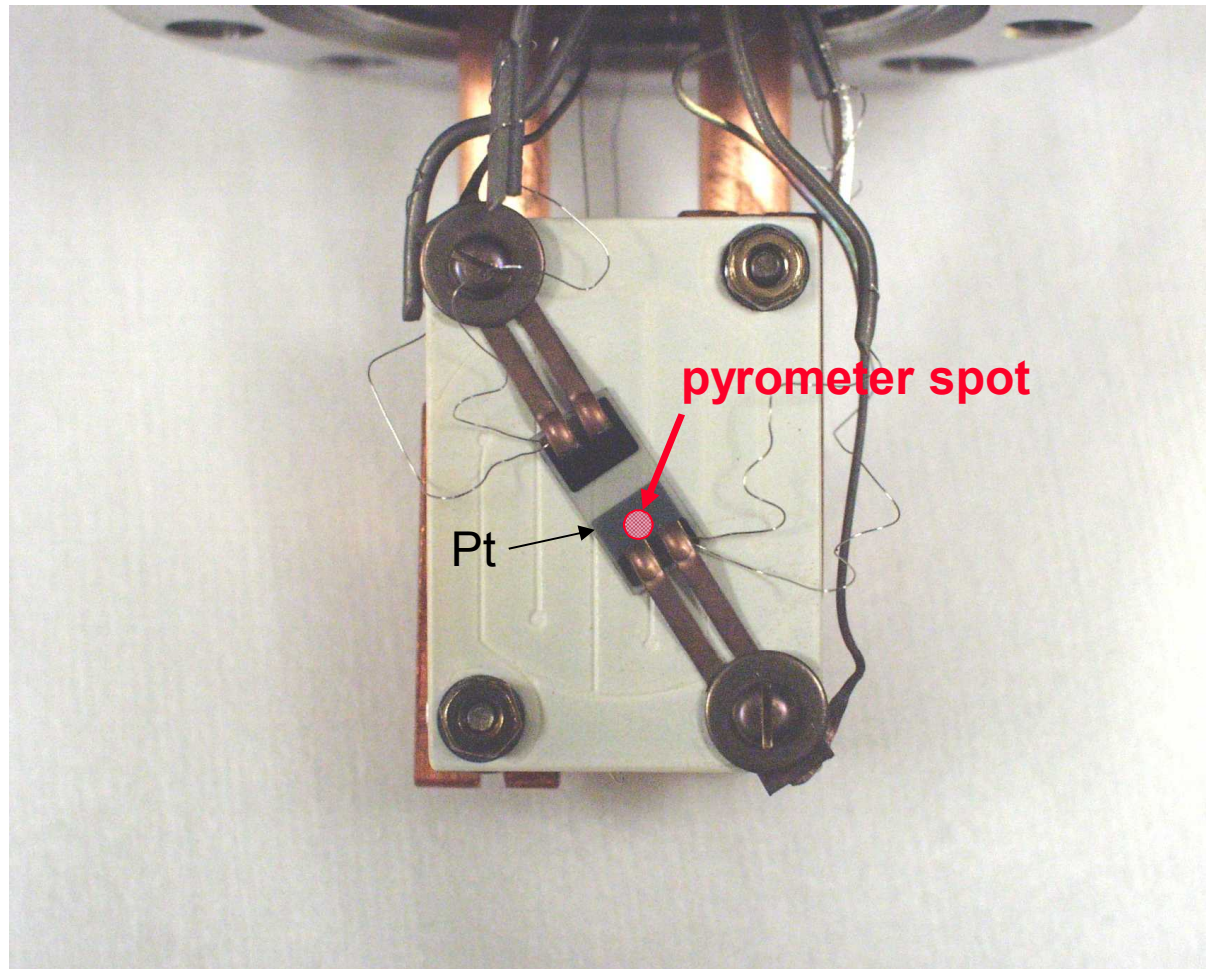
Full 3D simulation



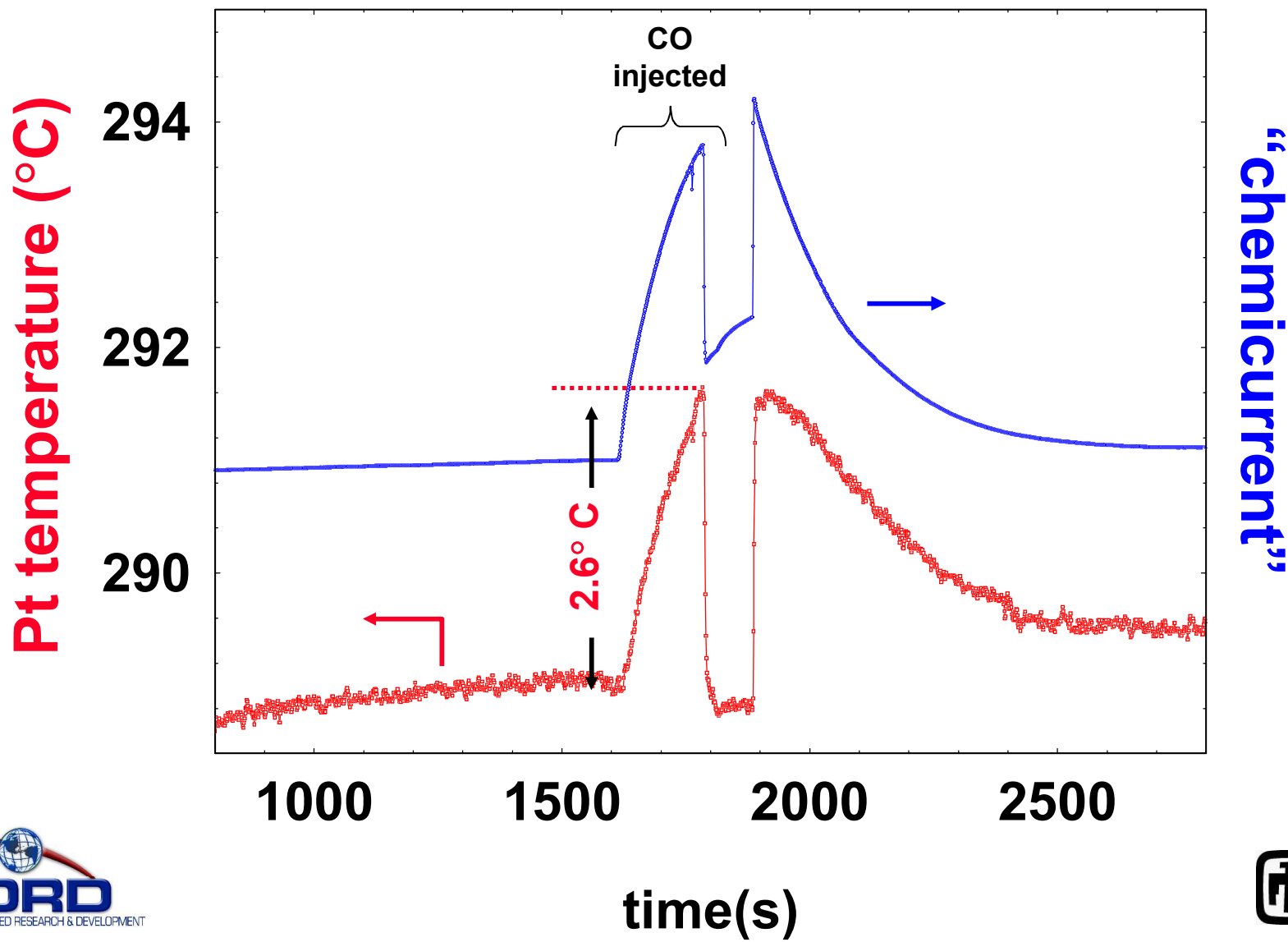
Heater at
constant
power

Experimental methods of temperature measurement

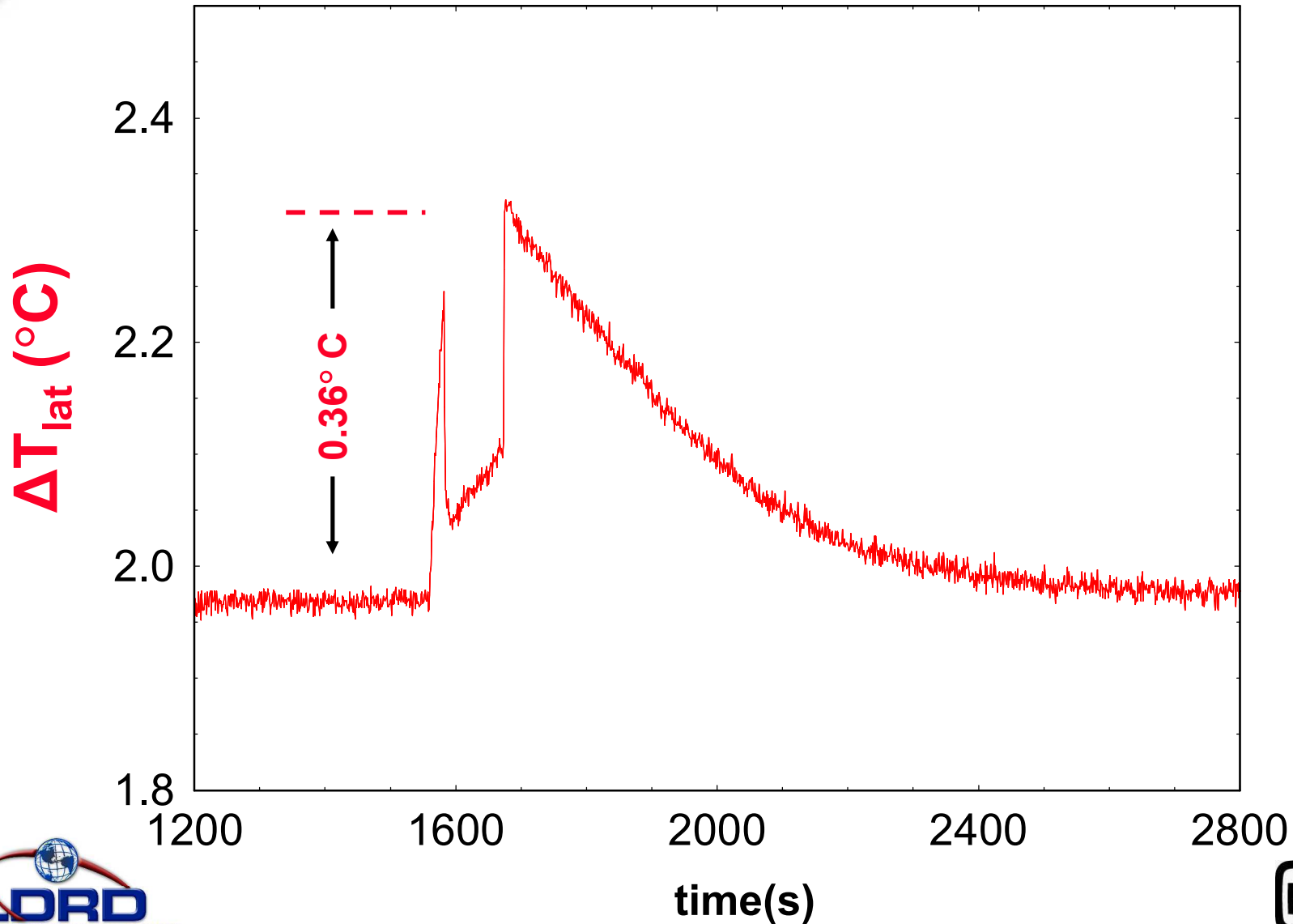
Nanodiode mounted with thermocouples on contacts



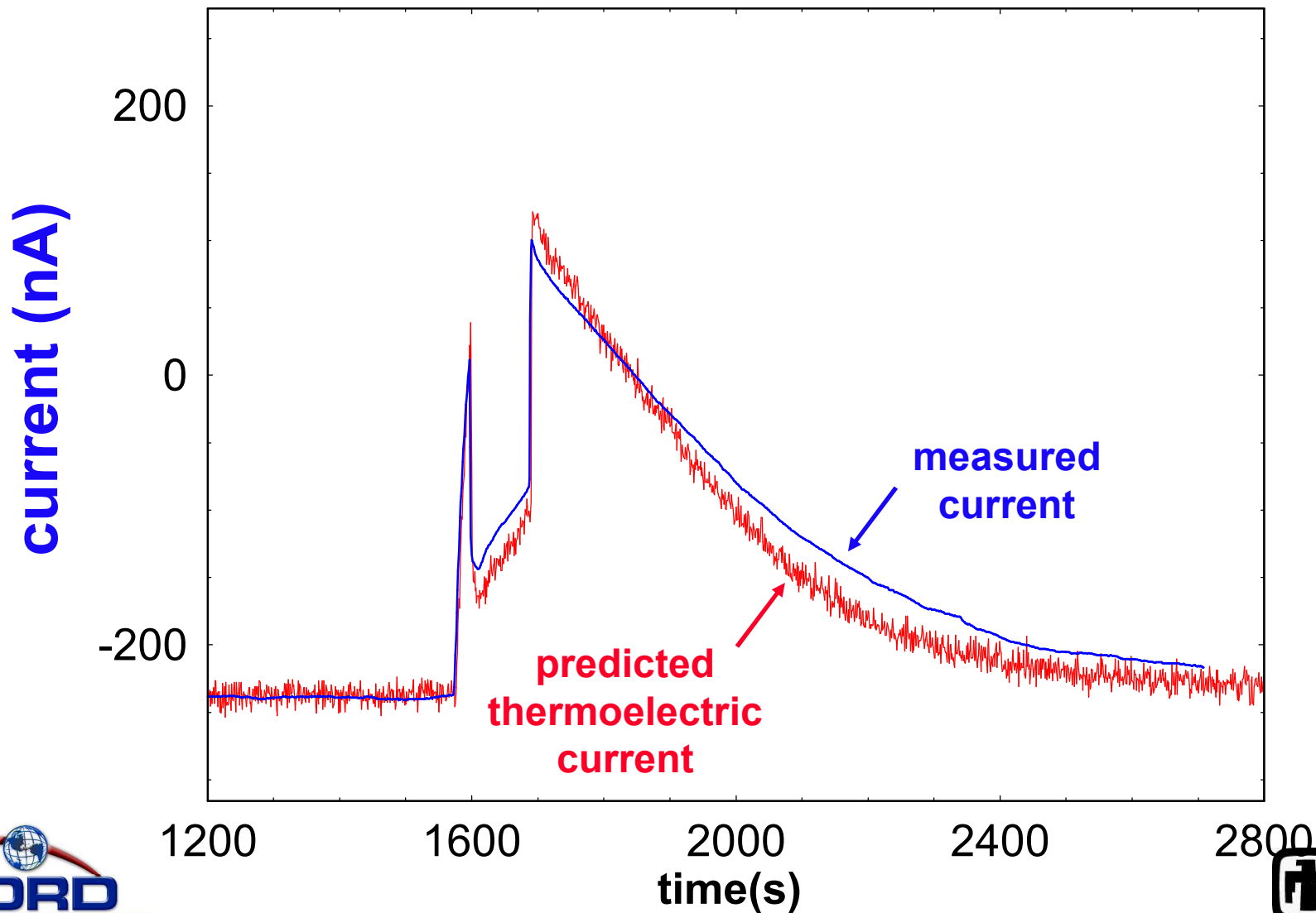
mid-IR (7.5 μm) pyrometer unambiguously measures
Pt surface temperature rise during reaction




thermocouples are used to measure the lateral temperature gradient during reaction



Observed current can be quantitatively explained using ΔT_{lat} , the Seebeck Coef, and the diode resistance, it is entirely due to thermoelectric voltage





Our calculations and measurements conclusively demonstrate surface temperature rises of a **1-5 °C**, and lateral temperature gradients of **0.2-1.0 °C**

In contrast, Park et al. (Top Cat 2007) concluded that the temperature increase during reaction was negligible (**< 10⁻³ °C**), and therefore **dismissed the thermoelectric effect**

→ They only considered the vertical temperature gradient within the thin Pt and TiO₂ layers (**ΔT_{\perp}**), which significantly underestimates the temperature changes from the reaction exothermicity



Summary

- We have fabricated Pt/GaN and Pt/TiO₂ nanodiodes that exhibit **unmistakable kinetic signatures** of the CO + O₂ reaction, **the electronic signal is derived from the chemical reaction**
- However, the signal dependence on diode shunt resistance indicates that it is **derived from a voltage source**
- With appropriate temperature calculations & measurements, all attributes of the chemical signal can be qualitatively and quantitatively explained by reaction exothermicity and the **thermoelectric properties** of the diode
- measured current is thermoelectric in origin **it is not true chemicurrent**